

# SIDC03D65C8

# Fast switching diode chip in EMCON 3 -Technology

#### Features:

- 650V EMCON 3 technology 65 µm chip
- · Soft, fast switching
- Low reverse recovery charge
- Small temperature coefficient
- Qualified according to JEDEC for target applications

#### Recommended for:

- Power module
- Discrete components



### **Applications:**

- Drives
- White goods
- Resonant applications

Chip Type	$V_{R}$	<i>I</i> <sub>Fn</sub> <sup>1)</sup>	Die Size	Package
SIDC03D65C8	650V	10A	1.82 x 1.82 mm <sup>2</sup>	sawn on foil

nominal forward current at Tc = 100°C, not subject to production test - verified by design/characterisation

## **Mechanical Parameters**

Weenanical Landines	010			
Die size		1.82 x 1.82		
Area total		3.31	$\text{mm}^2$	
Anode pad size		1.39 x 1.39		
Thickness		65	μm	
Wafer size		200	mm	
Max. possible chips pe	er wafer	8499		
Passivation frontside		Photoimide		
Pad metal		3200 nm AlSiCu		
Backside metal		Ni Ag –system		
Die bond		Electrically conductive epoxy glue and soft solder		
Wire bond		Al, ≤500μm		
Reject ink dot size		Ø 0.65mm; max 1.2mm		
Storage environment	for original and sealed MBB bags	Ambient atmosphere air, Temperature 17°C – 25°C < 6 month		
	for open MBB bags	Acc. to IEC62258-3: Atmosphere >99% Nitrogen or ine Humidity <25%RH, Temperature 17°C – 25°C, < 6 m		



# SIDC03D65C8

# **Maximum Ratings**

Parameter	Symbol	Condition	Value	Unit
Repetitive peak reverse voltage	V <sub>RRM</sub>	T <sub>vj</sub> = 25 °C	650	V
Continuous forward current	I <sub>F</sub>	<i>T</i> <sub>vj</sub> < 150°C	1)	_
Maximum repetitive forward current <sup>2)</sup>	I <sub>FRM</sub>	<i>T</i> <sub>vj</sub> < 150°C	20	A
Operating junction temperature	T <sub>vj</sub>		-40+175	°C

<sup>1)</sup> depending on thermal properties of assembly

# **Static Characteristics** (tested on wafer), $T_{vj}$ = 25 °C

Parameter	Symbol	Conditions	Value			Unit
raiailletei		Conditions	min.	typ.	max.	Oilit
Reverse leakage current	$I_{R}$	V <sub>R</sub> =650V			0.14	μA
Cathode-Anode breakdown Voltage	V <sub>BR</sub>	I <sub>R</sub> =0.25mA	650			V
Forward voltage drop	V <sub>F</sub>	$I_F = 10 A$	1.23	1.55	1.87	

# Electrical Characteristics (not subject to production test - verified by design/characterization)

Parameter	Symbol	Conditions	Value			Unit
Parameter		Conditions	min.	typ.	max.	Oiiit
Forward voltage drop	V <sub>F</sub>	$I_{\rm F} = 10{\rm A}, \ T_{\rm vj} = 150^{\circ}{\rm C}$		1.5		V

#### **Further Electrical Characteristics**

Switching characteristics and thermal properties are depending strongly on module design and mounting technology and can therefore not be specified for a bare die.

This chip data sheet refers to the device data sheet	tbd	tbd
--	-----	-----

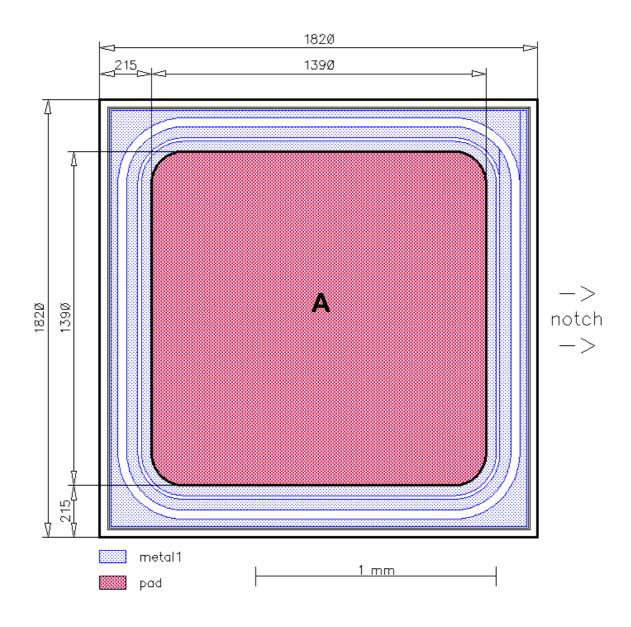
<sup>&</sup>lt;sup>2)</sup> not subject to production test - verified by design/characterisation





# **Chip Drawing**

Die-Size 1820 um x 1820 um



# A: Anode pad

Edited by INFINEON Technologies, IFAG IMM PSD D, L4014C, Edition 1.0, 12.09.2011



# SIDC03D65C8

Description
AQL 0,65 for visual inspection according to failure catalogue
Electrostatic Discharge Sensitive Device according to MIL-STD 883

### **Revision History**

Version	Subjects (major changes since last revision)	Date

Published by Infineon Technologies AG 81726 Munich, Germany © 2011 Infineon Technologies AG All Rights Reserved.

### **Legal Disclaimer**

The information given in this document shall in no event be regarded as a guarantee of conditions or characteristics. With respect to any examples or hints given herein, any typical values stated herein and/or any information regarding the application of the device, Infineon Technologies hereby disclaims any and all warranties and liabilities of any kind, including without limitation, warranties of non-infringement of intellectual property rights of any third party.

#### Information

For further information on technology, delivery terms and conditions and prices, please contact the nearest Infineon Technologies Office (www.infineon.com).

### **Warnings**

Due to technical requirements, components may contain dangerous substances. For information on the types in question, please contact the nearest Infineon Technologies Office.

The Infineon Technologies component described in this Data Sheet may be used in life-support devices or systems and/or automotive, aviation and aerospace applications or systems only with the express written approval of Infineon Technologies, if a failure of such components can reasonably be expected to cause the failure of that life-support, automotive, aviation and aerospace device or system or to affect the safety or effectiveness of that device or system. Life support devices or systems are intended to be implanted in the human body or to support and/or maintain and sustain and/or protect human life. If they fail, it is reasonable to assume that the health of the user or other persons may be endangered.

Edited by INFINEON Technologies, IFAG IMM PSD D, L4014C, Edition 1.0, 12.09.2011

单击下面可查看定价,库存,交付和生命周期等信息

>>Infineon Technologies(英飞凌)